Scaling of the conductivity of Si:B: Anomalous crossover in a magnetic field

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The zero-temperature conductivity of Si:B with dopant concentrations near the metal-insulator transition exhibits scaling as a function of magnetic field with an anomalously large crossover exponent. The large value of $d$ is associated with unusual behavior of the magnetoconductance, which vanishes as a power law approaching the transition. This demonstrates that Si:B, which has an anomalous critical conductivity exponent in zero field, also exhibits unusual behavior in response to a magnetic field.

Based on a number of experimental results, most notably the elegant measurements to very low temperatures by Paalanen et al. $^1$ in stress-tuned Si:P, the metal-insulator transition that occurs in doped semiconductors and amorphous metal-semiconductor mixtures is generally believed to be a continuous phase transition. $^2$ Various physical properties, such as the conductivity and the Hall coefficient, are expected to satisfy appropriate scaling relations as the transition is approached, and their critical behavior has been extensively studied in a variety of materials. $^3$ Despite considerable experimental and theoretical progress, there are a number of interesting unresolved issues in this area that continue to receive a great deal of attention. In particular, while most amorphous metal-insulator mixtures and most doped semiconductors, such as Ge:Sb, $^4,5$ have critical conductivity exponents near 1, the silicon-based materials Si:P, $^1$ Si:B, $^6$ and Si:As (Ref. 7) exhibit anomalously small conductivity exponents between $\frac{1}{2}$ and $\frac{1}{3}$. $^8$ A number of suggestions have been advanced to resolve this enigma, but none has gained general acceptance. $^8,10$

The response to an external magnetic field of systems characterized by a critical conductivity exponent $\mu=1$ was investigated by Rosenbaum, Field, and Bhatt. $^{11}$ They showed that the conductivity of Ge:Sb, a system that exhibits the widely observed zero-field conductivity exponent $\mu=1$, obeys scaling with concentration and magnetic field with the crossover exponent $\delta=\frac{1}{2}$ predicted theoretically by Khmel’nitskii and Larkin. $^{12}$ In contrast, we show in this paper that the transport in a magnetic field of Si:B, a material that exhibits a zero-field conductivity exponent smaller than 1, is highly anomalous. The data for the zero-temperature conductivity in various magnetic fields of several samples of Si:B with different dopant concentrations lie on a single curve, but with a crossover exponent $\delta$ that is much larger than 1. This anomalously large value can be traced to the unusual concentration dependence of the magnetoconductance approaching the metal-insulator transition. Thus, two systems Ge:Sb and Si:B, which have different zero-field conductivity exponents, exhibit an even larger difference in their magnetic-field crossover exponent.

Seven metallic Si:B samples with dopant concentrations 4.11, 4.20, 4.30, 4.38, 4.56, 4.75, and 4.97 $\times 10^{18}$ cm$^{-3}$ were measured at temperatures between 0.06 and 0.5 K in magnetic fields to 9 T. Sample characterization and measurement techniques are described in detail elsewhere. $^{13}$ The conductivity of a typical sample is shown as a function of $T^{1/2}$ in various fixed magnetic fields in Fig. 1.

The determination of the magnetic-field crossover exponent requires extrapolations of the measured values of the conductivity to zero temperature. We have recently shown $^{14}$ that the magnetoconductance of Si:B obeys a universal relation consistent with the general form expected for

![Graph](image)

**FIG. 1.** For a typical metallic Si:B sample with boron concentration $4.38 \times 10^{18}$ cm$^{-3}$, the conductivity $\sigma(n,H,T)$ is plotted as a function of $T^{1/2}$ at various fixed magnetic fields, as labeled. The lines (see text) yield zero-temperature conductivities, $\sigma(n,H,0)$ plotted in Fig. 2.
spin splitting that is approximately independent of dopant

...{\sigma(n,0,0)}/\sigma(n,0,0) = 1 - m_H(n)H^{1/2}/\sigma_0(\Delta n/n_c)^\mu. \tag{4}

Here \(\Delta n = (n-n_c)\), \(n_c\) is the critical concentration and \(\mu\) is the critical conductivity exponent in zero field. Scaling \(^1\text{,}^{2,16}\) with magnetic field requires

\[
\sigma(n,H,0)/\sigma(n,0,0) = G(H^{-\delta}\Delta n) = F(H/H^*) \tag{5}
\]

with a power law dependence of \(H^*\) on \(\Delta n\) in the critical region of the form

\[
H^* \approx \Delta n^{1/\delta}. \tag{6}
\]

Setting \(B = A/\sigma_0\) and \(x = H^{1/[2(\mu-\alpha)]}(\Delta n/n_c)\), comparison of Eqs. (4) and (5) yields a crossover function \(G(x) = 1 - B^{1/(\delta-\alpha)}\) and crossover exponent \(\delta = 1/2(\mu-\alpha)\). Using \(\mu = 0.65\) for Si:B (Ref. 5) and \(\alpha = 0.37\), one obtains \(\delta = 1.8\), consistent with the value obtained from the fit to inset (a) of Fig. 2.

The ratio \(\sigma(n,H,0)/\sigma(n,0,0)\) is shown as a function of magnetic field \(H\) on a log-log scale in Fig. 3(a); Fig. 3(b) demonstrates that all the curves can indeed be brought into coincidence by appropriate choices of \(H^*\), corresponding to different rigid horizontal shifts for each sample. The inset to Fig. 3(b) shows \(H^*\) versus \(\Delta n = (n-n_c)\) on a log-log scale. Deviations from a straight line are evident at the highest dopant concentration, indicating that the critical region is restricted: it extends no higher than \(n = 1.20n_c\), and probably only the four samples closest to the transition, or \(n \approx 1.10n_c\), in agreement with a recent suggestion of Stupp et al.\(^9\) The exponent \(\delta\) can be obtained from the inverse of the slope of the straight line region of inset (b). It depends on the breadth assumed for the critical range, as well as on the choice of the critical concentration \(n_c\) for which \(n_c = 4.01 \times 10^{18}\) cm\(^{-3}\); fits to four, five, or six data points yield \(\delta = 2.2\) and \(1.8\), and \(1.65\), respectively. Equivalent fits for a much lower \(n_c = 3.90 \times 10^{18}\) cm\(^{-3}\) yield \(\delta = 1.4\), \(1.2\), and \(1.15\). All reasonable assumptions thus yield values for the crossover exponent that are well above 1, consistent with the superlinear behavior of \(\Delta n\) shown in Fig. 2, inset (a).

We now compare our findings with existing theories. The observation of scaling suggests that the dopant concentration
and the magnetic field enter the conductivity through two lengths larger than the microscopic distances, namely, the localization length $\xi$ and a magnetic length $l_H$. When orbital effects dominate, the conductivity is determined by the flux threading an area $\approx \xi^2$, the scaling function depends on $B\xi^2$ and the magnetic crossover exponent $\delta$ is given by $1/(2\nu)$. This was first argued by Khmeľ’nički i and Larkin; it is in fact quite general and follows from the gauge invariance of the coupling of the vector potential to the metallic order parameter. In the absence of any complicating factors, rigorous bounds\(^{18}\) on the exponent $\nu$ then imply that $\delta$ must be less than 0.75. Magnetic-field coupling to the spin degrees of freedom can produce another crossover exponent. Still, approximate calculations for noninteracting electrons\(^{19}\) and for interacting electrons\(^{20}\) yield a value of $\delta$ that is even smaller than for orbital effects. It is important to note, however, that the large crossover exponent in Si:B is associated with the unusual concentration dependence of the magnetoconductance and the value $\delta=1.7$ does not violate any theoretical bound.

The crossover behavior of the conductivity in a magnetic field has been investigated experimentally in Si:As by Shafarman et al.\(^{21}\) and in Ge:Sb by Rosenbaum, Field, and Bhatt.\(^{11}\) No definitive value of the crossover exponent was obtained for Si:As, where the observed behavior was attributed to changes in the critical exponent and to field-tuning of the critical concentration. On the other hand, it is instructive to compare the behavior of Si:B with that found for Ge:Sb,\(^{11}\) which has a distinctly different crossover exponent $\delta=1/2$. The zero-field conductivity of Ge:Sb vanishes with the usual exponent $\mu\approx1$, and a magnetic field does not modify its value substantially.\(^{5,11}\) The zero-temperature conductivity obeys Eq. (2) with a slope $m_H(n)$ that is constant and independent of concentration ($\alpha=0$). If plotted in Fig. 2, this would yield a set of parallel lines of equal slope for different dopant concentrations. Thus, the magnetoconductance of Ge:Sb is nonzero and negative (positive magnetoresistance) for any metallic sample, no matter how close its concentration to the critical value $n_c$; here a magnetic field drives any metallic sample toward the insulating phase.\(^{23}\) The conductivity exhibits scaling as a function of magnetic field with a crossover exponent $\delta=1/[2(\mu-\alpha)]=1/2$, consistent with expectations for systems in which orbital effects dominate. The dependence of the critical concentration on $H$ is sublinear (square root), varying strongly with $H$ at small fields. In contrast, the critical conductivity exponent of Si:B has an anomalously low value\(^6\) of $\mu=0.65$ in zero field (changing to the value 1 in a magnetic field\(^21\)). The magnetoconductance $m_H(n)$ of Si:B (the slopes in Fig. 2) depends strongly on dopant concentration and decreases continuously as a power law to zero at $n_c$. Near the transition, a magnetic field drives the system neither toward insulating nor toward metallic behavior. The critical concentration exhibits a superlinear dependence on field with an anomalously large crossover exponent near 2. Thus, the large value of the crossover exponent of Si:B is associated with the very unusual behavior of its magnetoconductance.

To summarize, we show that Si:B, one of the prototypical silicon-based semiconductors whose anomalous behavior in zero field has long been an unresolved puzzle, also exhibits unusual behavior in response to a magnetic field. Its zero-temperature conductivity exhibits scaling as a function of magnetic field with an anomalously large crossover exponent $\delta$. The large value of $\delta$ can be traced to the vanishing of the magnetoconductance amplitude approaching the metal-insulator transition. We note that measurements\(^{24}\) of the susceptibility of Si:B have shown that the response of the spin degrees of freedom to a magnetic field becomes stronger as we approach the metal-insulator transition. Our paper demonstrates that the response of the charge degrees of freedom to an external magnetic field, namely, the magnetoresistance, shows the opposite behavior, becoming weaker as the transition is approached. To the best of our knowledge, there is currently no theoretical explanation for these experimental findings, which we hope will stimulate theoretical developments.

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FIG. 3. (a) The ratio $\sigma(n,H,0)/\sigma(n,0,0)$ versus magnetic field $H$ on a log-log scale for seven Si:B samples with dopant concentrations as labeled. (b) Scaled curves of $\sigma(n,H,0)/\sigma(n,0,0)$ versus $H/H^*$ on a log-log plot. The inset shows $H^*$ versus $\Delta n=(n-n_c)$ on a log-log scale for $n_c=4.01\times10^{18}$ cm$^{-3}$. The solid and dashed lines represent fits, respectively, to four and to six dopant concentrations nearest the metal-insulator transition.

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For a recent review, see D. Belitz and T. R. Kirkpatrick, Rev. Mod. Phys. 66, 261 (1994).


We note, however, that H. Stupp, M. Hornung, M. Lakner, O. Madel, and H. v. Lohneysen, Phys. Rev. Lett. 71, 2634 (1993), have recently suggested that analysis of data for samples very near the transition yields $\mu \approx 1.3$.

